

RJP4003ANS

Nch IGBT for Strobe Flash

REJ03G1474-0100 Rev.1.00 Oct 13, 2006

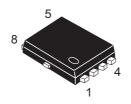
Features

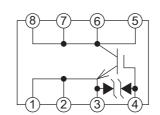
• Ultra small surface mount package (VSON-8)

V_{CES}: 400 V
 I_{CM}: 150 A
 Drive voltage: 4 V

Outline

RENESAS Package code: PVSN0008JA-A (Package name: VSON-8<TNP-8DBV>)





1, 2, 3 : Emitter 4 : Gate 5, 6, 7, 8 : Collector

Applications

Strobe flash for cameras

Maximum Ratings

 $(Tc = 25^{\circ}C)$

Parameter	Symbol	Ratings	Unit	Conditions
Collector-emitter voltage	V _{CES}	400	V	V _{GE} = 0 V
Gate-emitter voltage	V _{GES}	±6	V	V _{CE} = 0 V
Peak gate-emitter voltage	V_{GEM}	±8	V	$V_{CE} = 0 \text{ V}, \text{ tw} = 10 \text{ s}$
Collector current (Pulse)	I _{CM}	150	А	$C_M = 400 \mu F$ (see performance curve)
Junction temperature	Tj	- 40 to +150	°C	
Storage temperature	Tstg	- 40 to +150	°C	

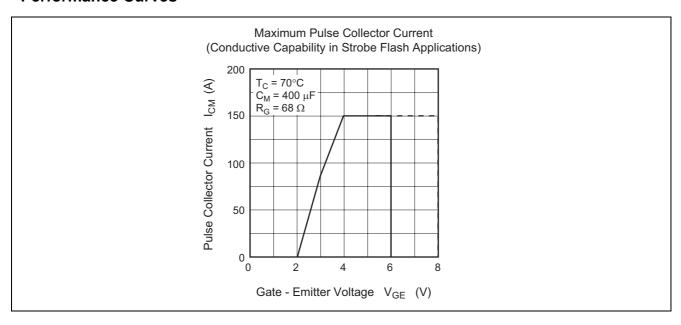
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Electrical Characteristics

 $(Tj = 25^{\circ}C)$

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions
Collector-emitter breakdown voltage	$V_{(BR)CES}$	450	_	_	V	$I_C = 1 \text{ mA}, V_{GE} = 0 \text{ V}$
Collector-emitter leakage current	I _{CES}	_	_	10	μΑ	$V_{CE} = 400 \text{ V}, V_{GE} = 0 \text{ V}$
Gate-emitter leakage current	I_{GES}	_	_	±10	μΑ	$V_{GE} = \pm 6 \text{ V}, V_{CS} = 0 \text{ V}$
Gate-emitter threshold voltage	$V_{\text{GE(th)}}$	0.5	0.7	1.5	V	$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ mA}$
Collector-emitter saturation voltage	$V_{CE(sat)}$	_	5.0	10.0	V	$I_C = 150 \text{ A}, V_{GE} = 4 \text{ V}$
Input capacitance	Cies	_	5000	_	pF	$V_{CE} = 25 \text{ V}, V_{GE} = 10 \text{ V},$
						f = 1 MHz

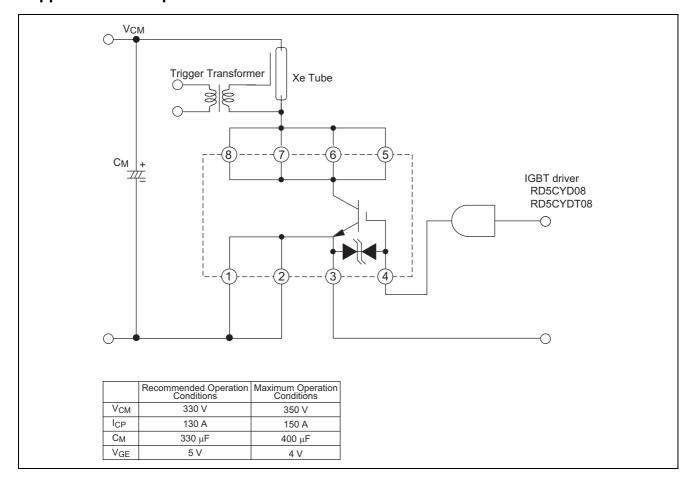
Performance Curves



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Application Example

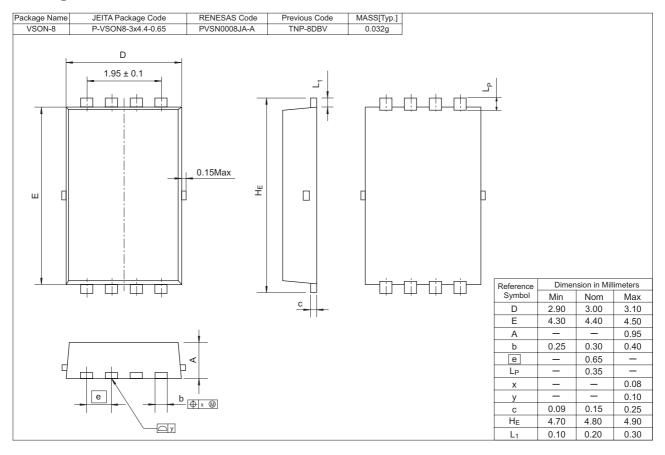


Precautions on Usage

- 1. IGBT has MOS structure and its gate is insulated by thin silicon oxide. So please handle carefully to protect the device from electrostatic charge.
- 2. Gate drive voltage during on-period must be applied to satisfy the rating of maximum pulse collector current. And www.DataSturn4off.dv/dt must become less than 400 V/ μ s. In general, when $R_{G (off)} = 68 \Omega$, it is satisfied.
 - 3. The ground of the drive signal must be connected to pin 3 only. If the emitter terminal pins 1 and 2 in which a large currents flow are given to the device as the drive signal emitter, the device may be damaged due to large currents since the specified gate voltage is not applied to the IGBT within the device.
 - 4. The operation life should be endured until repeated discharge of 5,000 times under the charge current ($I_{Xe} \le 150~A$: full luminescence condition) of main capacitor ($C_M = 400~\mu F$). Repetition period under full luminescence condition is over 3 seconds.
 - 5. Total operation hours applied to the gate-emitter voltage must be within 5,000 hours when V_{GE} is driven at 6 V.

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Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	3000	Type name – 00 – Q1	RJP4003ANS-00-Q1

Note: Please confirm the specification about the shipping in detail.

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Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

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Renesas Technology America, Inc.

www.DataSl h4504holgemWay, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510